HM62W4100HC Series

4M High Speed SRAM (1-Mword × 4-bit)

HITACHI

ADE-203-1202 (Z)
Preliminary
Rev. 0.0
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Description

The HM62W4100HC is a 4-Mbit high speed static RAM organized 1-Mword × 4-bit. It has realized high speed access time by employing CMOS process (6-transistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed and high density memory, such as cache and buffer memory in system. The HM62W4100HC is packaged in 400-mil 32-pin SOJ for high density surface mounting.

Features

- Single supply : 3.3 V ± 0.3 V
- Access time : 10 ns (max)
- Completely static memory
  - — No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
  - — All inputs and outputs
- Operating current : 115 mA (max)
- TTL standby current : 40 mA (max)
- CMOS standby current : 5 mA (max)
  : 1 mA (max) (L-version)
- Data retension current : 0.6 mA (max) (L-version)
- Data retension voltage: 2 V (min) (L-version)
- Center V_{CC} and V_{SS} type pinout

Preliminary: The specification of this device are subject to change without notice. Please contact your nearest Hitachi's Sales Dept. regarding specification.

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